

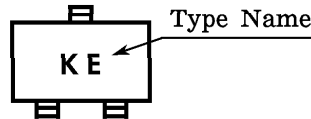
TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK1062

HIGH SPEED SWITCHING APPLICATIONS
 ANALOG SWITCHING APPLICATIONS
 INTERFACE APPLICATIONS

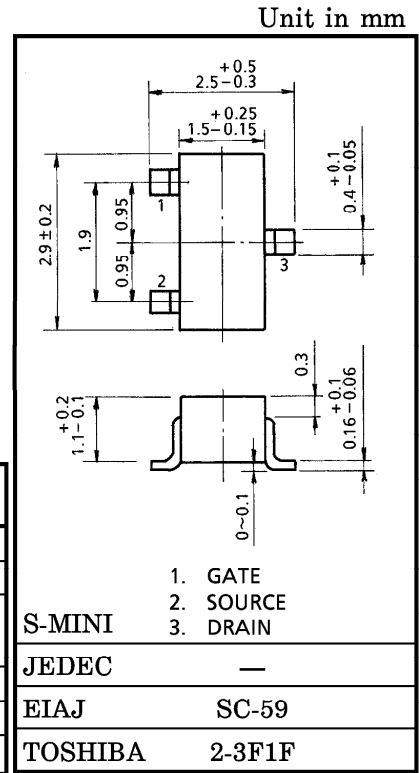
- Excellent Switching Time : $t_{on} = 14\text{ns}$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 100\text{mS}$ (Min.) @ $I_D = 50\text{mA}$
- Low On Resistance : $R_{DS(ON)} = 0.6\Omega$ (Typ.) @ $I_D = 50\text{mA}$
- Enhancement-Mode
- Complementary to 2SJ168.

Marking



MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	200
	Pulse	I_{DP}	800
Drain Power Dissipation ($T_a = 25^\circ\text{C}$)	P_D	200	mW
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight : 0.012g

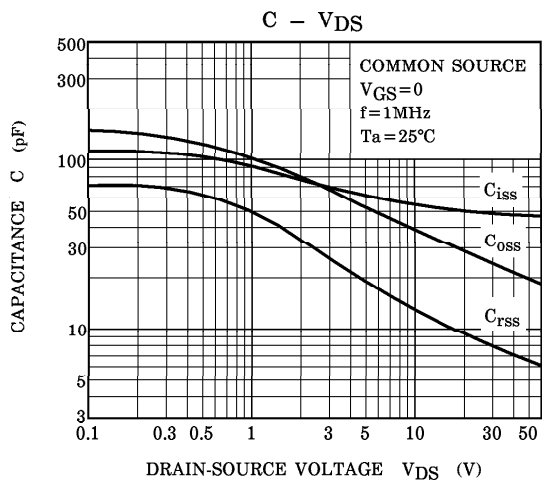
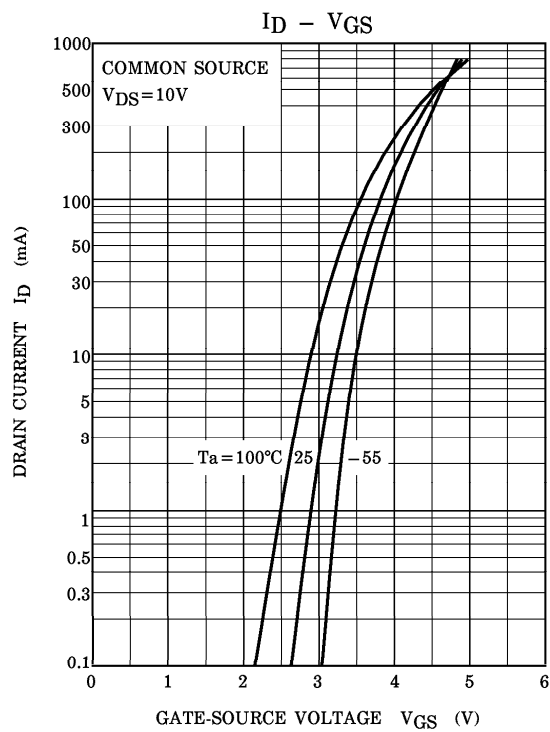
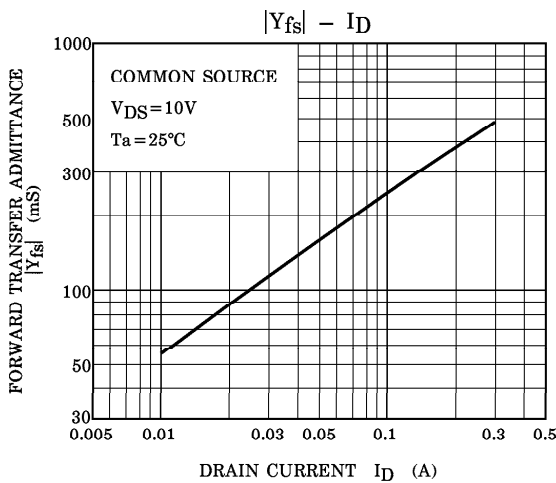
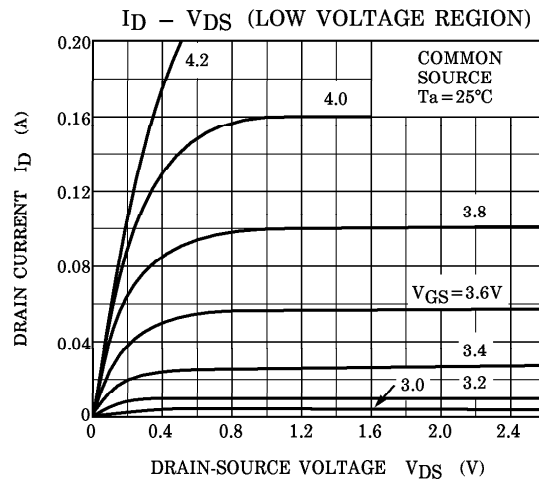
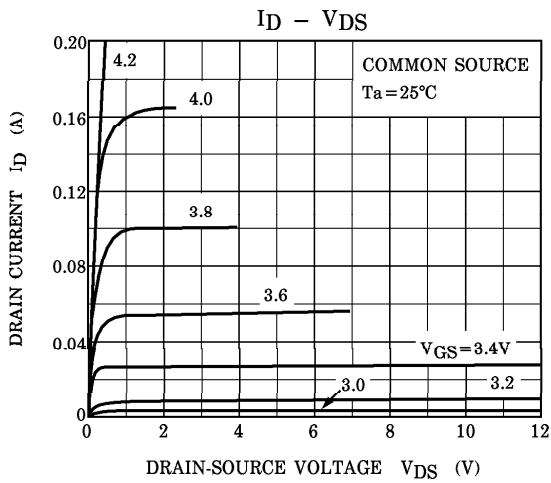
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 10\text{V}, V_{DS} = 0$	—	—	± 100	nA		
Drain Cut-off Current	I_{DSS}	$V_{DS} = 60\text{V}, V_{GS} = 0$	—	—	10	μA		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	60	—	—	V		
Gate Threshold Voltage	V_{th}	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	2	—	3.5	V		
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 50\text{mA}$	100	—	—	mS		
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D = 50\text{mA}, V_{GS} = 10\text{V}$	—	0.6	1.0	Ω		
Drain-Source ON Voltage	$V_{DS(ON)}$	$I_D = 50\text{mA}, V_{GS} = 10\text{V}$	—	30	50	mV		
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	55	65	pF		
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	13	18	pF		
Output Capacitance	C_{oss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	40	50	pF		
Switching Time	Rise Time	t_r				—	8	—
	Turn-on Time	t_{on}				—	14	—
	Fall Time	t_f				—	35	—
	Turn-off Time	t_{off}				—	75	—

This transistor is the electrostatic sensitive device. Please handle with caution.

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